IN THE SPECIFICATION:

Please amend the paragraph beginning on page 8, line 31, as follows:

--As shown in Fig. 4, ~~Co atoms 31~~ Co atoms 31a, Pt atoms 32 and SiO_2 molecules 33 are allowed to fall on the surface of the substrate 21 under the vacuum atmosphere in the sputtering apparatus. The rate of the SiO_2 molecules 33 may be set in a range between 5at% and 20at% of the total amount of the ~~Co atoms 31~~ Co atoms 31a, the Pt atoms 32 and the SiO_2 molecules 33.--

Please amend the paragraph beginning on page 9, line 6, as follows:

--As shown in Fig. 5, the ~~Co atoms 31~~ Co atoms 31a, the Pt atoms 32 and the SiO_2 molecules 33 form the fine metallic nucleation sites 27 sparsely existing over the surface of the substrate 21. In this case, the substrate 21 is maintained at the normal temperature in the sputtering apparatus. The growth of the individual nucleation sites 27 is restrained. The density of the nucleation sites 27 per unit area can significantly be increased. On the other hand, if the nucleation sites 27 are subjected to heat, the growth of the individual nucleation sites 27 is promoted based on aggregation due to a higher temperature. The individual nucleation sites 27 grow bigger. The nucleation sites 27 are distanced from each other.--

Please amend the paragraph beginning on page 10, line 14, as follows:

--When the high frequency glow discharge has begun, the Co atoms 31, the Pt atoms 32 and the SiO_2 molecules 33 are sputtered out of the target 39. the ~~Co atoms 31~~ Co atoms 31a, the Pt atoms 32 and the SiO_2 molecules 33 are allowed to fall on the substrate 21 on the anode 41. The ~~Co atoms 31~~ Co atoms 31a, the Pt atoms 32 and the SiO_2 molecules 33 thus form the fine metallic nucleation sites 27 on the surface of the substrate 21. If the content of SiO_2 drops below 5at%, the formation of the nucleation sites 27 cannot be achieved. On the other hand, if the content of SiO_2 exceeds 20at%, the formed nucleation sites 27 are covered with the SiO_2 layer. The nucleation sites 27 under the SiO_2 layer cannot contribute to a subsequent growth of crystal grains. The content of the ~~Co atoms 31~~ Co atoms 31a, the Pt atoms 32 and the SiO_2 molecules 33b in the nucleation sites 27 corresponds to that of the target 39.--

Please amend the paragraph beginning on page 10, line 29, as follows:

--As shown in Fig. 7, a disk-shaped block 43 of CoPt alloy may be employed as a target 42 in the sputtering apparatus 35 for example. Chips 44 of SiO_2 are located on the surface of the block 43. The content of the atoms ~~31~~31a, 32 and the molecules 33 can be determined based on the ratio of the exposed area between the block 43 and the chips 44.

Otherwise, a CoPt alloy area 46 and an SiO_2 area 47 may be defined side by side on a target 45, as shown in Fig. 8.--

Please amend the paragraph beginning on page 11, line 26, as follows:

--The output power of the DC power source 52 serves to determine the amount of falling ~~Co atoms 31~~ Co atoms 31a and Pt atoms 32 in the co-sputtering apparatus 48. Likewise, the output power of the RF power source 53 serves to determine the amount of falling SiO_2 molecules 33. Adjustment of the output powers leads to an easier management of the content within the nucleation sites 27 irrespective of the size or exposed areas of the target 54, 55. The co-sputtering apparatus 48 only requires a pair of targets, independently including a CoPt alloy and SiO_2. If the content between the CoPt alloy and SiO_2 is intended to be set at 95:5 in at%, the output power of the DC power source 52 is set at approximately 100W while the output power of the power source 53 is set at approximately 50W, for example. The operation time may be set at 1[sec] in this case.--